

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L3	10498	semiconductor and (resistor resistance) with (silicide silicided silicidation)	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/07/26 08:32
L4	11020	semiconductor and (resistor resistance) with (silicide silicided silicidation salicide salicidation salicided)	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/07/26 08:40
L5	3398	4 and (resistor resistance) with (substrate)	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/07/26 08:22
L6	710	5 and (after post) near5 (silicide silicided silicidation salicide salicidation salicided)	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/07/26 08:21
L7	41	6 and (measur\$5) near5 (silicide silicided silicidation salicide salicidation salicided)	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/07/26 08:23
L8	82	6 and measur\$3 with (resistor resistance silicide silicided silicidation salicide salicidation salicided)	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/07/26 08:34
L9	1	10/605439	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/07/26 08:23
L10	19734	(resistor resistance) with (polysilicon polycrystalline polysi polysilicon)	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/07/26 08:39
L11	372	6 and 10	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/07/26 08:33
L12	19	7 and 11	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/07/26 08:34

L13	22005	(resistor resistance resistivity) with (polysilicon polycrystalline polysi polysilicon)	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/07/26 08:49
L14	5558	13 and (resistor resistance resistivity) with (silicide silicided silicidation salicide salicidation salicided policide)	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/07/26 09:46
L15	4725	14 and (annealing anneal\$3 heat\$3 heating thermal\$5)	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/07/26 08:43
L16	1909	15 and (after post) with (silicide silicided silicidation salicide salicidation salicided policide)	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/07/26 08:45
L18	1567	16 and (implanting implantation implant\$3)	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/07/26 08:48
L20	1268	18 and temperature	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/07/26 08:47
L22	1156	20 and (implanting implantation implant\$3) with (dopant ion)	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/07/26 08:49
L23	123	22 and measur\$5 with (resistor resistance resistivity)	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/07/26 09:47
L24	250	22 and value with (resistor resistance resistivity)	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/07/26 08:50
L25	5	"6436747"	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/07/26 08:55
L26	3	"6027964"	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/07/26 08:55

L27	17	"5656524"	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/07/26 09:00
L28	0	10/711130	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/07/26 09:00
L29	5802	13 and (resistor resistance resistivity) with (silicide silicided silicidation salicide salicidation salicided polycide)	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/07/26 09:46
L30	107	polysilicon near3 resistor.ti.	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/07/26 09:47

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